



FORM PTO-1449(Modified)  LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	ATTY. DOCKET NO.: K1-02US1	SERIAL NO.: 10/772,673
	APPLICANT: Jan Kuzmik	
	FILING DATE: February 5, 2004	GROUP:

## U.S. PATENT DOCUMENTS

Exam Unit	Ref Des	Document No.	Date	Name	Class	Sub Class	FILING DATE If Appropriate
		3,764,865	10/9/73	Napoli et al	257	283	3/17/70
		3,767,984	10/23/73	Shinoda et al	257	268	9/13/72
		3,855,690	12/24/74	Kim et al	438	180	12/26/72
		3,861,024	1/21/75	Napoli et al	438	301	4/12/73
		3,943,622	3/16/76	Kim et al	438	180	10/22/74
		4,030,942	6/21/77	Keenan et al	438	526	10/28/75
		4,075,652	2/21/78	Umebachi et al	257	192	5/5/77
		4,157,556	6/5/79	Decker et al	257	280	1/6/77
		4,163,984	8/7/79	Pucel	257	285	1/27/78
		4,173,764	11/6/79	de Cremoux	257	192	4/4/78
		4,325,181	4/20/82	Yoder	438	180	12/17/80
		4,424,525	1/3/85	Mimura	257	194	12/29/80
		4,593,301	6/3/86	Inata et al	257	194	3/1/85
		4,642,879	2/17/87	Kawata et al	438	174	11/28/83
		4,714,948	12/22/87	Mimura et al	257	194	3/13/86
		4,912,451	3/27/90	Sugiyama et al	338	32	12/29/88
		4,961,194	10/2/90	Kuroda et al	257	192	12/21/89
		4,980,731	12/25/90	Hida	257	192	1/13/90
		5,021,857	6/4/91	Suehiro	257	392	11/29/89
		5,041,393	8/20/91	Ahrens et al	438	172	12/28/88
		5,084,743	1/28/92	Mishra et al	257	487	3/15/90
		5,153,682	10/6/92	Goto et al	257	194	2/25/91
		5,180,681	1/19/93	Mishra et al	438	167	10/22/91
		5,192,987	3/9/93	Khan et al	257	183.1	5/17/91
		5,262,660	11/16/93	Streit et al	257	194	8/1/91
		5,288,654	2/22/94	Kasai et al	438	577	2/8/93
		5,312,765	5/17/94	Kanber	438	59	5/11/93
		5,352,909	10/4/94	Hori	257	76	12/14/92
		5,358,878	10/25/94	Suchet et al	438	172	3/9/92
		5,359,220	10/25/94	Larson et al	257	378	12/22/92
		5,365,080	11/15/94	Yamazaki et al	257	66	2/14/94
		5,411,914	5/2/95	Chen et al	438	167	5/15/92

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<del>100</del>		5,447,874	9/5/95	Grivna et al	438	174	7/29/94
<del>100</del>		5,471,077	11/28/95	Sokolich	257	192	10/10/91
<del>100</del>		5,486,705	1/23/96	Inoue et al	257	24	6/9/94
<del>100</del>		5,493,136	2/20/96	Matsuzaki et al	257	287	2/17/94
<del>100</del>		5,521,403	5/58/96	Usui et al	257	192	4/6/95
<del>100</del>		5,521,404	5/28/96	Kikkawa et al	257	194	12/9/94
<del>100</del>		5,554,865	9/10/96	Larson	257	275	6/7/95
<del>100</del>		5,596,211	1/21/97	Onda et al	257	194	10/18/95
<del>100</del>		5,611,955	3/18/97	Barrett et al	252	62.3	10/18/93
<del>100</del>		5,652,440	7/29/97	Chang	257	194	9/8/95
<del>100</del>		5,668,387	9/16/97	Streit et al	257	192	10/26/97
<del>100</del>		5,696,387	12/9/97	Choi et al	257	57	5/58/96
<del>100</del>		5,698,900	12/16/97	Bozada et al	257	744	7/22/96
<del>100</del>		5,739,558	4/14/98	Ishida et al	257	192	1/21/97
<del>100</del>		5,811,843	9/22/98	Yamanamoto et al	257	194	2/24/97
<del>100</del>		5,811,844	9/22/98	Kuo et al	257	194	7/3/97
<del>100</del>		5,821,825	10/13/98	Kobayashi	331	66	11/26/96
<del>100</del>		5,831,277	11/3/98	Razeghi	257	15	3/19/97
<del>100</del>		5,834,796	11/10/98	Matsuda et al	257	57	5/24/96
<del>100</del>		5,847,414	12/8/98	Harris et al	257	77	8/18/97
<del>100</del>		5,856,217	1/5/99	Nguyen et al	438	172	4/10/97
<del>100</del>		5,880,491	3/9/99	Soref et al	257	190	1/31/97
<del>100</del>		5,900,653	5/4/99	Suzuki et al	257	194	4/15/97
<del>100</del>		5,929,467	7/27/99	Kawai et al	257	192	12/3/97
<del>100</del>		5,976,920	11/2/99	Nakano et al	438	172	7/22/96
<del>100</del>		6,049,091	4/11/00	Yokoyama	257	52	6/30/97
<del>100</del>		6,049,097	4/11/00	Hida	257	192	7/24/95
<del>100</del>		6,057,566	5/2/00	Heisenbeiser et al	257	194	4/29/98
<del>100</del>		6,064,082	5/16/00	Kawai et al	257	192	5/29/98
<del>100</del>		6,100,542	8/8/00	Kohara et al	257	20	11/19/97
<del>100</del>		6,140,169	10/31/00	Kawai et al	438	197	4/1/99
<del>100</del>		6,177,685	1/23/01	Teraguchi et al	257	20	1/20/99
<del>100</del>		6,214,678	4/10/01	Docter et al	438	285	5/21/97

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## U.S. PATENT DOCUMENTS

Exam Unit	Ref Des	Document No.	Date	Name	Class	Sub Class	FILING DATE If Appropriate
<del>100</del>		6,232,624	5/15/01	Matloubian et al	257	194	7/12/99
<del>100</del>		6,242,293	6/5/01	Danzilio	438	172	11/18/98
<del>100</del>		6,242,766	6/5/01	Tateno	257	194	11/18/99
<del>100</del>		6,316,793	11/13/01	Sheppard et al	257	103	6/12/98
<del>100</del>		6,355,951	3/12/02	Hattori	257	280	12/16/99
<del>100</del>		6,392,253	5/21/02	Saxena	257	59	8/6/99
<del>100</del>		6,429,467	8/6/02	Ando	257	194	1/27/00
<del>100</del>		6,444,552	9/3/02	Docter et al	438	542	7/15/99
<del>100</del>		6,465,289	10/15/02	Streit et al	438	167	7/1/96
<del>100</del>		6,515,316	2/4/03	Wojtowicz et al	257	194	7/4/00
<del>100</del>		6,524,899	2/25/03	Grundbacher et al	438	167	9/21/00
<del>100</del>		6,531,718	3/11/03	Inoue et al	257	189	1/12/01
<del>100</del>		6,583,454	6/24/03	Sheppard et al	257	194	3/29/01
<del>100</del>		6,646,293	11/11/03	Emrick et al	257	194	7/18/01
<del>100</del>		6,727,531	4/27/04	Redwing et al	257	194	8/7/00
<del>100</del>		20010020700	9/13/01	Inoue, et al	257	20	1/12/01

## FOREIGN PATENT DOCUMENTS

	Country & Doc. No. (11)	Pub. Date (43)		Class	Sub Class	Translation Yes	No
<del>100</del>	JP2000223697	11/8/00	NEC Corp			X	
<del>100</del>	JP2001196575	9/13/01				X	
<del>100</del>	WO0059084	10/5/00	Matsushita Electric Corporation			X	

## OTHER ART

(Including Author, Title, Date, Pertinent Pages, Publication, Etc.)

<del>100</del>		Alekseev, E. and Pavlidis, D. "DC and high-frequency performance of AlGaIn/GaN Heterojunction Bipolar Transistors." <u>Solid State Electronics</u> . 44:245-252, 2000.
<del>100</del>		Ambacher, O., et. al., "Role of spontaneous and piezoelectric polarization on novel AlGaIn/GaN/InGaIn device structures." <u>Physica-Status-Solidi-B</u> . 216(1):381-9, 1999.

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			Foutz, B.E., et. al., "The influence of spontaneous and piezoelectric polarization on novel AlGa <sub>N</sub> /Ga <sub>N</sub> /InGa <sub>N</sub> device structures." <u>Mat. Res. Soc. Symp. Proc.</u> 572:501-6, 1999.
			Imanaga, S., Kawai, H., "One-dimensional simulation of charge control in a novel AlN/GaN insulated gate heterostructure field effect transistor with modulation doping." <u>Journal of Crystal Growth</u> . 189-190: 742-8, 1998.
			Hackenbuchner, S, Majewski, J.A., Zandler, G., and Vogl, P. "Polarization induced 2D hole gas in GaN/AlGa <sub>N</sub> heterostructures." <u>Journal of Crystal Growth</u> . 230: 607-610, 2000.
			International Search Report for International Application No. PCT/SK02/00018, Nov. 12, 2002: 6pp.
			Maeda, N. et. al., "Enhanced two-dimensional electron gas confinement effect on transport properties in AlGa <sub>N</sub> /InGa <sub>N</sub> /AlGa <sub>N</sub> double-heterostructures." <u>Physica-Status-Solidi-B</u> . 216(1):727-31, 1999.
			Valizadeh, P. "Al <sub>x</sub> Ga <sub>1-x</sub> N/GaN High Electron Mobility Transistor (HEMT)." Course report of EECS521 (High speed transistors), University of Michigan: Winter, 2002.

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